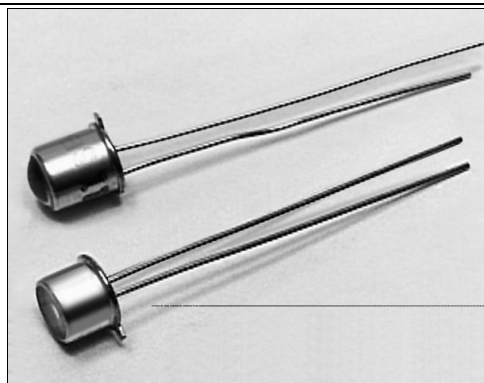


SE3450/5450

GaAs Infrared Emitting Diode

FEATURES

- TO-46 metal can package
- Choice of flat window or lensed package
- 90° or 20° (nominal) beam angle option
- 935 nm wavelength
- Wide operating temperature range (- 55°C to +125°C)
- Mechanically and spectrally matched to SD3421/5421 photodiode, SD3443/5443/5491 phototransistor, SD3410/5410 photodarlington and SD5600 series Schmitt trigger



INFRA-83.TIF

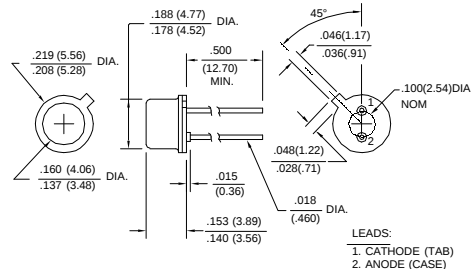
DESCRIPTION

The SE3450/5450 series consists of a gallium arsenide infrared emitting diode mounted in a TO-46 metal can package. The SE3450 series has flat window cans providing a wide beam angle, while the SE5450 series has glass lensed cans providing a narrow beam angle. The TO-46 packages offer high power dissipation capability and are ideally suited for operation in hostile environment.

OUTLINE DIMENSIONS in inches (mm)

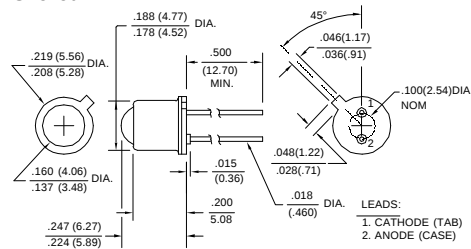
Tolerance	3 plc decimals	±0.005(0.12)
	2 plc decimals	±0.020(0.51)

SE3450



DIM_003a.ds4

SE5450



DIM_003b.ds4

SE3450/5450

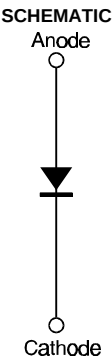
GaAs Infrared Emitting Diode

ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)						
PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Irradiance ⁽¹⁾ SE3450-011, SE5450-011 SE3450-012, SE5450-012 SE3450-013, SE5450-013 SE3450-014, SE5450-014	H	0.30 0.50 1.00 1.50			mW/cm²	I _F =100 mA
Forward Voltage	V _F			1.7	V	I _F =100 mA
Reverse Breakdown Voltage	V _{BR}	3.0			V	I _R =10 µA
Peak Output Wavelength	λ _p		935		nm	
Spectral Bandwidth	Δλ		50		nm	
Spectral Shift With Temperature	Δλ _p /ΔT		0.3		nm/°C	
Beam Angle ⁽²⁾ SE3450 SE5450	Ø		90 20		degr.	I _F =Constant
Radiation Rise And Fall Time	t _r , t _f		0.7		µs	

Notes
1. SE3450 measured into a 0.250 (6.35) diameter aperture placed 0.33(8.4) from window surface. SE5450 measured into a 0.250 (6.35) diameter aperture placed 1.20 (30.5) from lens tip.
2. Beam angle is defined as the total included angle between the half intensity points.

ABSOLUTE MAXIMUM RATINGS	
(25°C Free-Air Temperature unless otherwise noted)	
Continuous Forward Current	100 mA
Power Dissipation	150 mW ⁽¹⁾
Operating Temperature Range	-55°C to 125°C
Storage Temperature Range	-65°C to 150°C
Soldering Temperature (10 sec)	260°C

Notes
1. Derate linearly from 25°C free-air temperature at the rate of 1.43 mW/°C.



Honeywell reserves the right to make changes in order to improve design and supply the best products possible.

SE3450/5450

GaAs Infrared Emitting Diode

Fig. 1 Radiant Intensity vs Angular Displacement (SE3450) gra_017.ds4

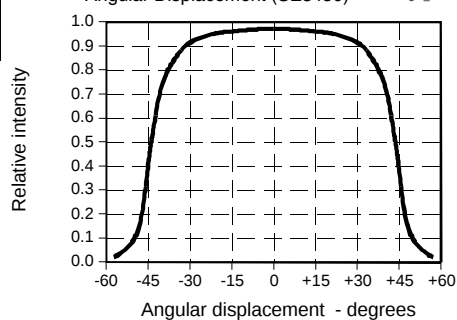


Fig. 2 Radiant Intensity vs Angular Displacement (SE5450) gra_023.ds4

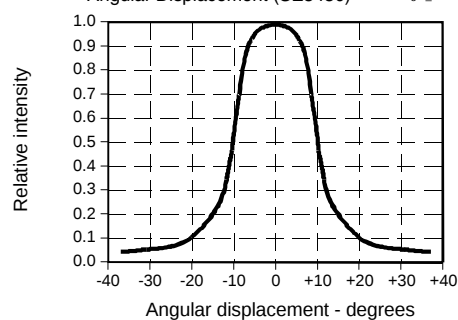


Fig. 3 Radiant Intensity vs Forward Current gra_018.ds4

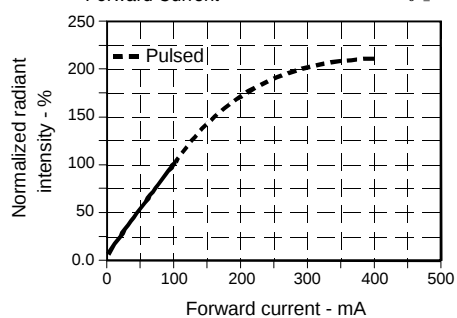


Fig. 4 Forward Voltage vs Forward Current gra_205.ds4

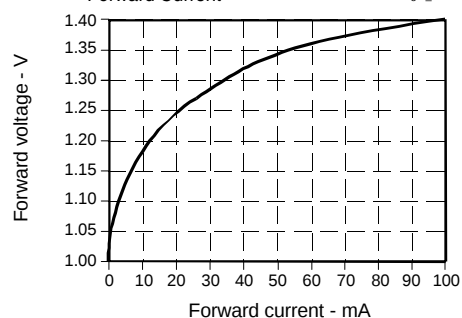


Fig. 5 Forward Voltage vs Temperature gra_206.ds4

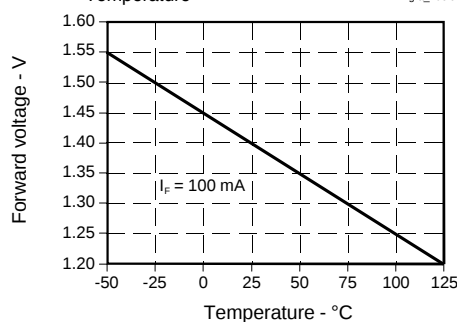
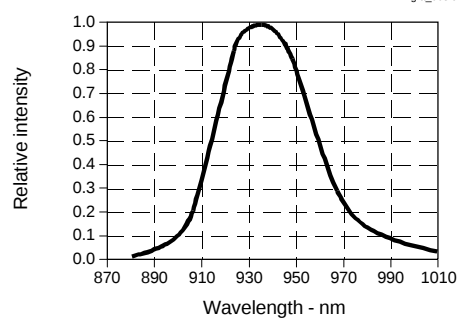


Fig. 6 Spectral Bandwidth gra_005.ds4



SE3450/5450

GaAs Infrared Emitting Diode

Fig. 7 Coupling Characteristics
SE3450 with SD3443

gra_021.ds4

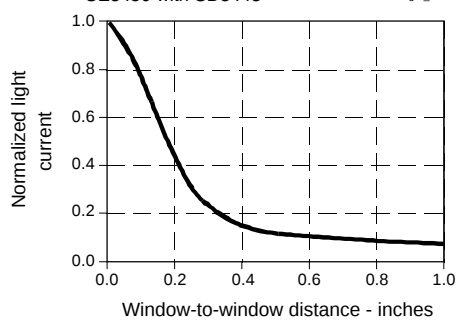


Fig. 8 Coupling Characteristics
SE5450 with SD5443

gra_024.ds4

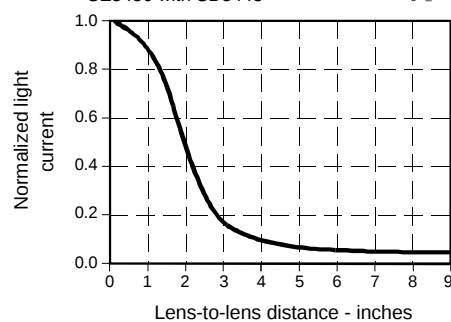
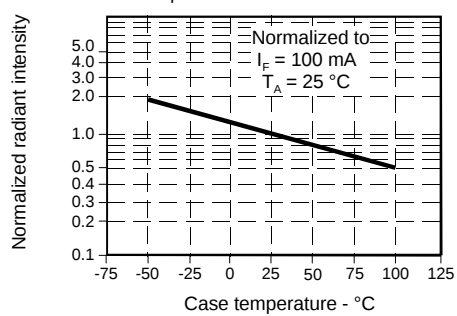


Fig. 9 Radiant Intensity vs
Case Temperature

gra_022.ds4



All Performance Curves Show Typical Values